650V Super-Junction Power MOSFET

DESCRIPTION

650V super-junction Power MOSFET

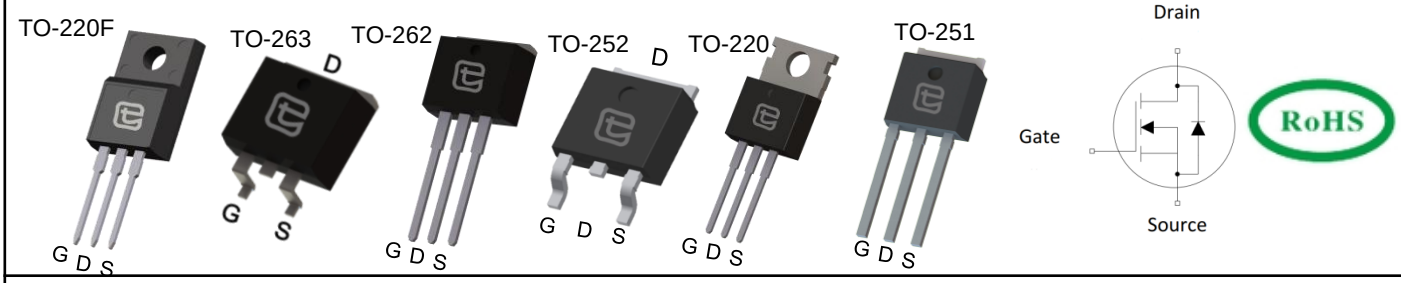
Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The SJ MOSFET is a price-performance optimized product enabling to target cost sensitive applications in Consumer and Lighting markets, designed by Wuxi Unigroup Microelectronics Company.

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
TPA65R450CFD	TO-220F	65R450CFD
TPB65R450CFD	TO-263	65R450CFD
TPC65R450CFD	TO-262	65R450CFD
TPD65R450CFD	TO-252	65R450CFD
TPP65R450CFD	TO-220	65R450CFD
TPU65R450CFD	TO-251	65R450CFD

Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	650	V
$R_{DS(on),max}$	0.45	Ω
I_D	11	A
$Q_{g,typ}$	20	nC
I_{DM}	33	A

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted					
Parameter		**Symbol**	**Value**		**Unit**
			TO-220,TO-251,TO-252 TO-262,TO-263	TO-220F	
Drain-Source Voltage (V_{GS} = 0V)		V_{DSS}	650		V
Continuous Drain Current	T_C = 25ºC	I_D	11		A
	T_C = 100ºC		6.6		
Pulsed Drain Current (note1)		I_{DM}	33		A
Gate-Source Voltage		V_{GSS}	±30		V
Single Pulse Avalanche Energy (note2)		E_{AS}	210		mJ
Avalanche Current		I_{AS}	1.6		A
Power Dissipation		P_D	78	31.3	W
Continuous Body Diode Current		I_S	11		A
Pulsed Diode Forward Current (note1)		I_{SM}	33		
MOSFET dv/dt ruggedness, V_{DS} = 0...960V		dv/dt	50		V/ns
Reverse diode dv/dt, V_{DS} = 0…960V, $I_{SD} \le I_D$		dv/dt	15		A/us
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150		ºC

Thermal Resistance				
Parameter	**Symbol**	**Value**		**Unit**
		TO-220,TO-251,TO-252 TO-262,TO-263	TO-220F	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.6	4	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	80	

Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
		V_{DS} = 650V, V_{GS} = 0V, T_J = 150ºC	--	--	5000	
Gate-Source Leakage	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	--	4.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 5.5A	--	0.38	0.45	Ω
Forward Transconductance (Note3)	g_{fs}	V_{DS} = 10V, I_D = 5.5A	--	7.8	--	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1.0MHz	--	902	--	pF
Output Capacitance	C_{oss}		--	49	--	
Reverse Transfer Capacitance	C_{rss}		--	5.3	--	
Total Gate Charge	Q_g	V_{DD} = 520V, I_D = 11A, V_{GS} = 10V	--	20	--	nC
Gate-Source Charge	Q_{gs}		--	4.3	--	
Gate-Drain Charge	Q_{gd}		--	6.9	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D = 11A, R_G = 25Ω	--	43	--	ns
Turn-on Rise Time	t_r		--	22	--	
Turn-off Delay Time	$t_{d(off)}$		--	121	--	
Turn-off Fall Time	t_f		--	6.5	--	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 11A, V_{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 480V, I_F = I_S, di_F/dt = 100A/μs	--	97	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.43	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	17	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. I_{AS}=1.6A,V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

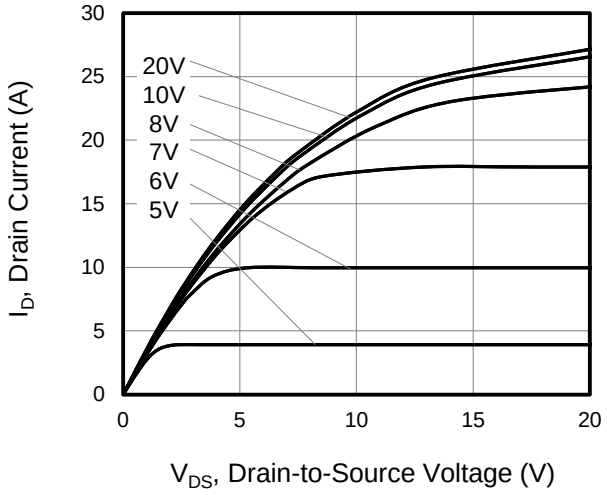


Figure 2. Transfer Characteristics

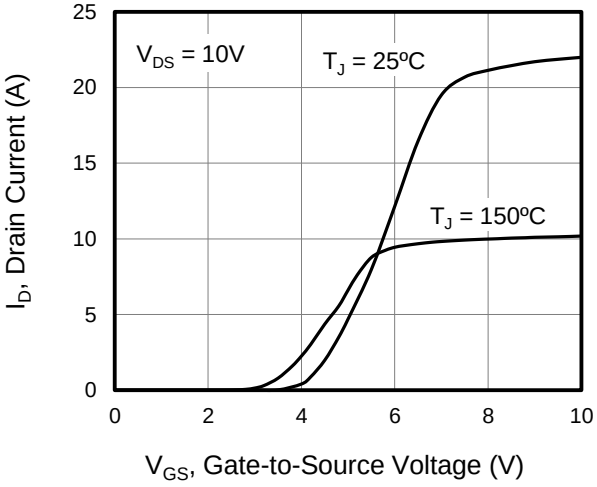


Figure 3. On-Resistance vs. Drain Current

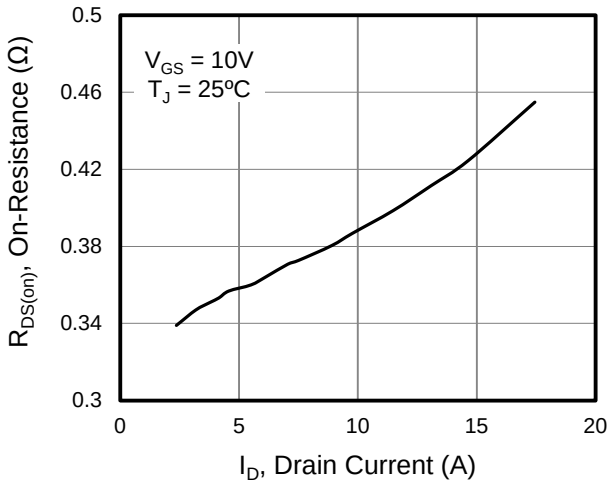


Figure 4. Capacitance

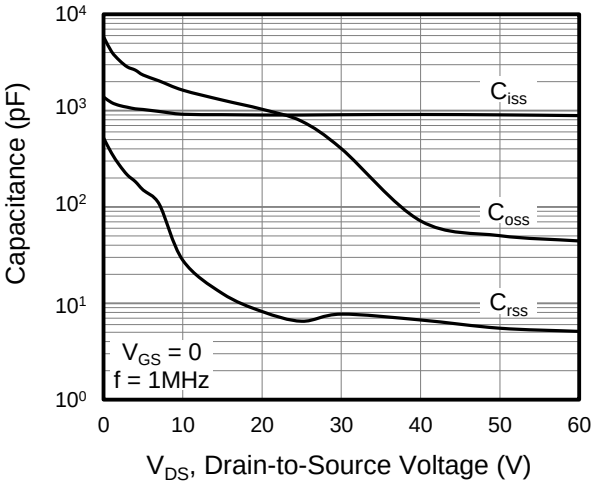


Figure 5. Gate Charge

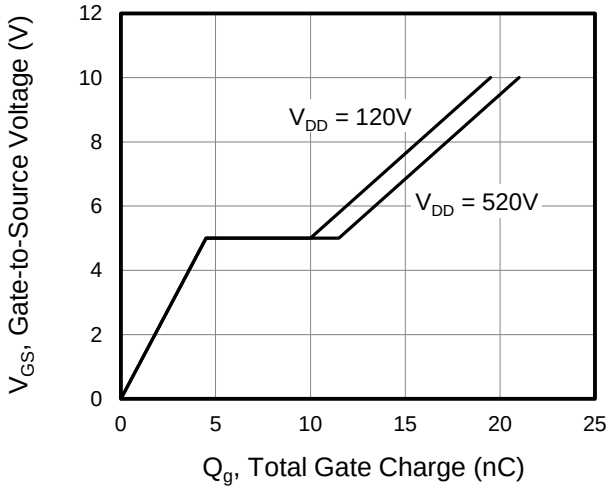
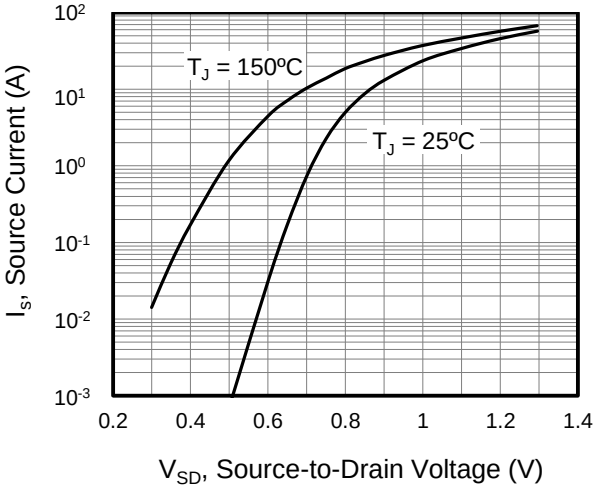


Figure 6. Body Diode Forward Voltage



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

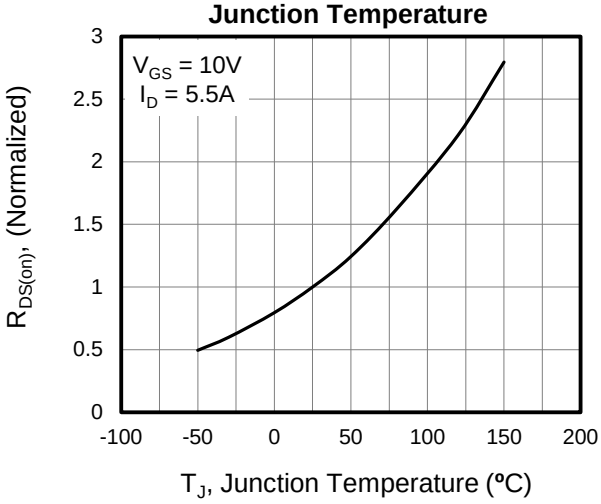


Figure 8. Breakdown voltage vs. Junction Temperature

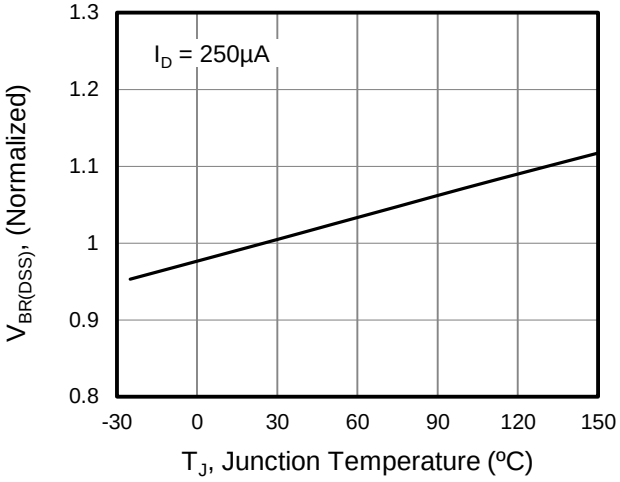


Figure 9. Transient Thermal Impedance TO-220,TO-262,TO-263,TO-251,TO-252

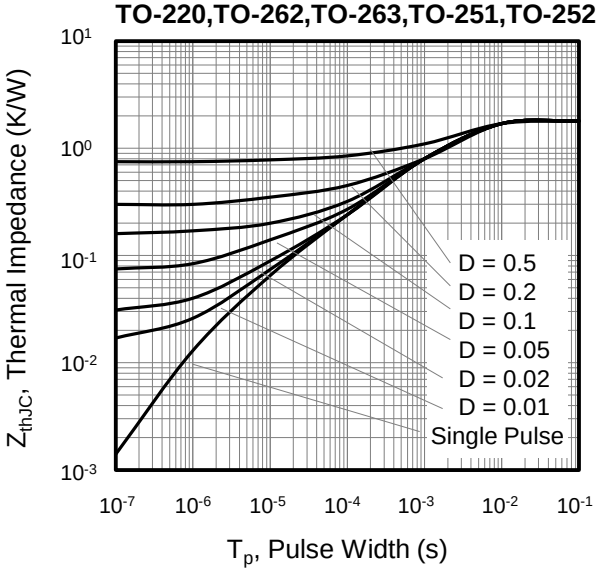


Figure 10. Transient Thermal Impedance TO-220F

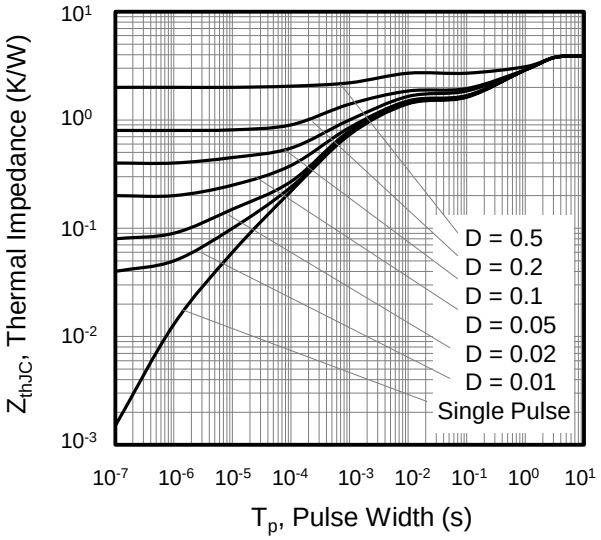


Figure 11. Safe operation area for TO-220,TO-262,TO-263,TO-251,TO-252

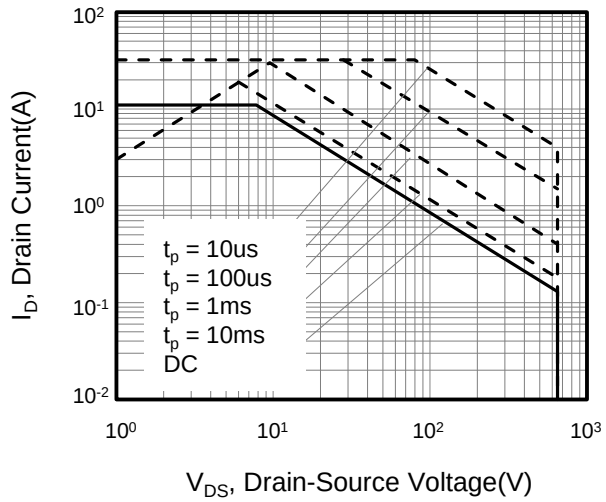


Figure 12. Safe operation area for TO-220F

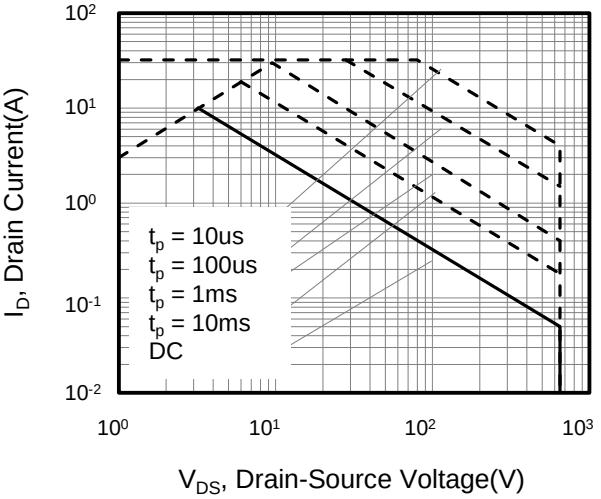


Figure A：Gate Charge Test Circuit and Waveform

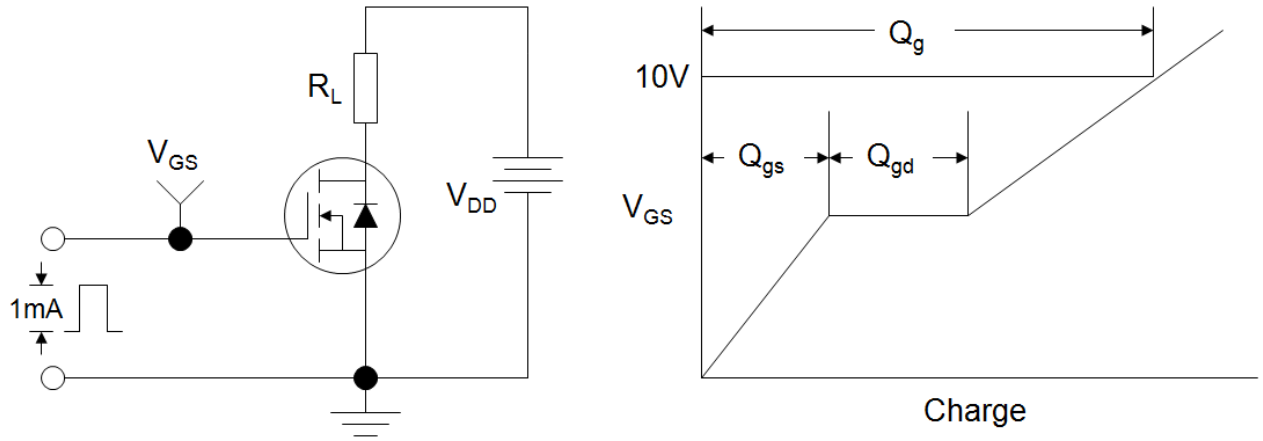


Figure B：Resistive Switching Test Circuit and Waveform

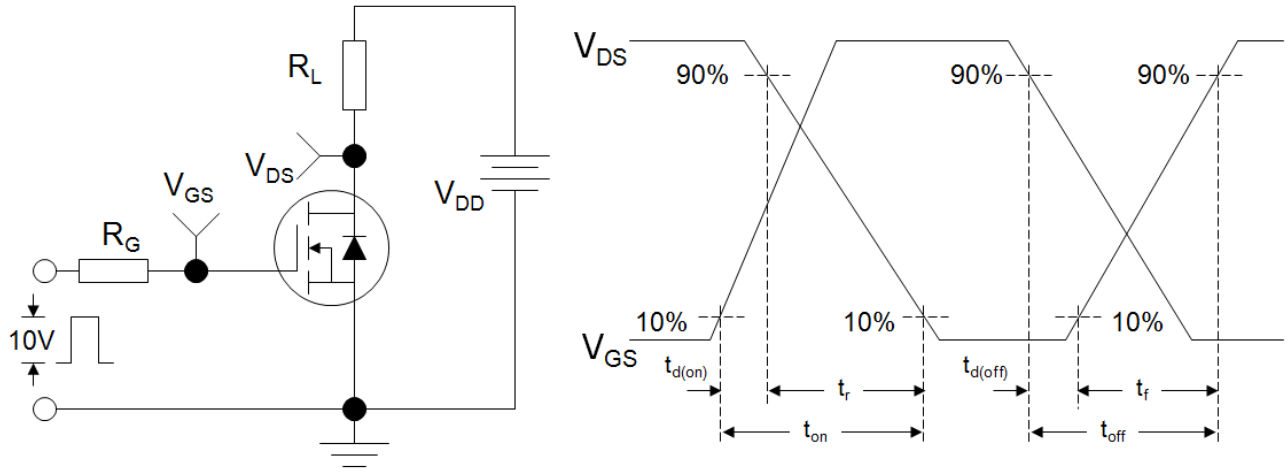
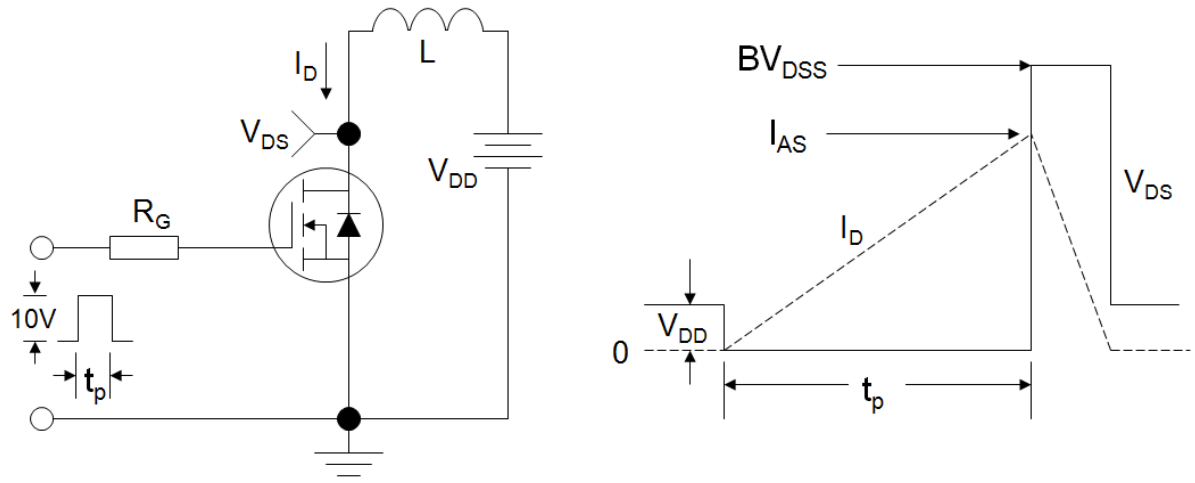
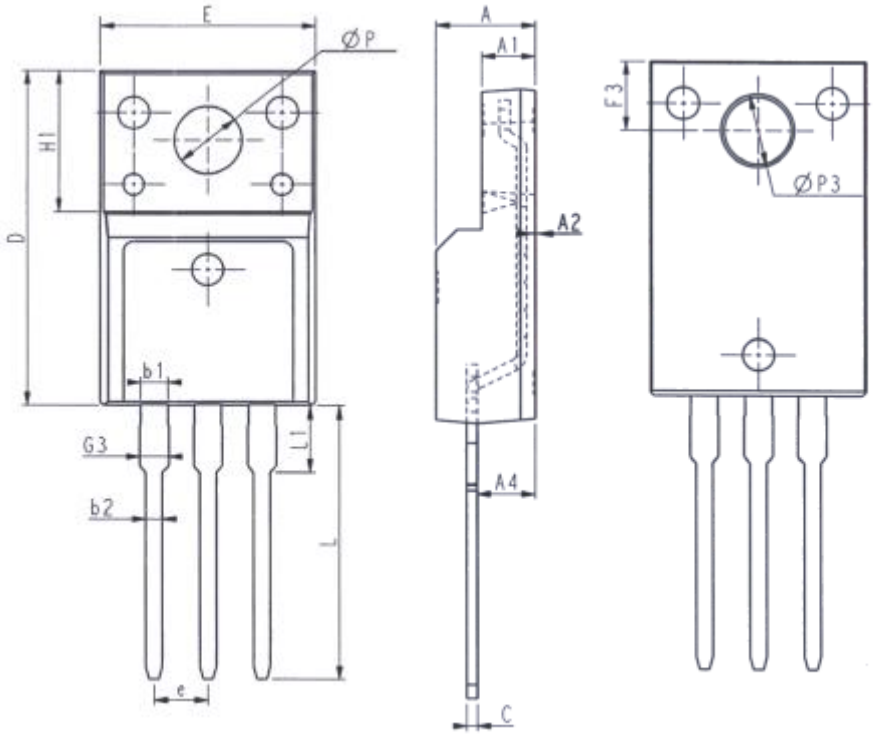


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



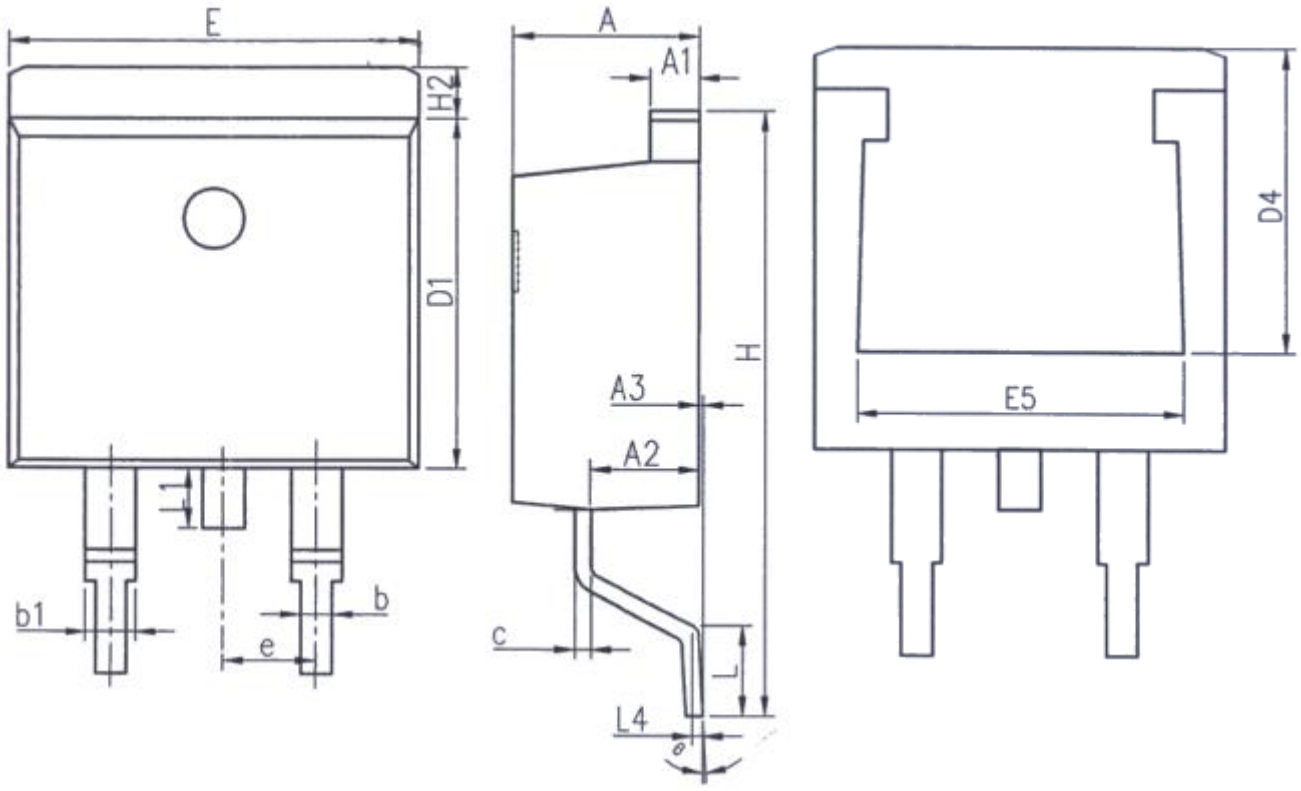
TO-220F



Unit: mm		
Symbol	Min.	Max.
E	9.96	10.36
A	4.50	4.90
A1	2.34	2.74
A2	0.30	0.60
A4	2.56	2.96
c	0.40	0.65
D	15.57	16.17
H1	6.70REF	
e	2.54BSC	

Unit: mm		
Symbol	Min.	Max.
L	12.68	13.28
L1	2.93	3.13
P	3.03	3.38
P3	3.15	3.65
F3	3.15	3.45
G3	1.25	1.55
b1	1.18	1.43
b2	0.70	0.95

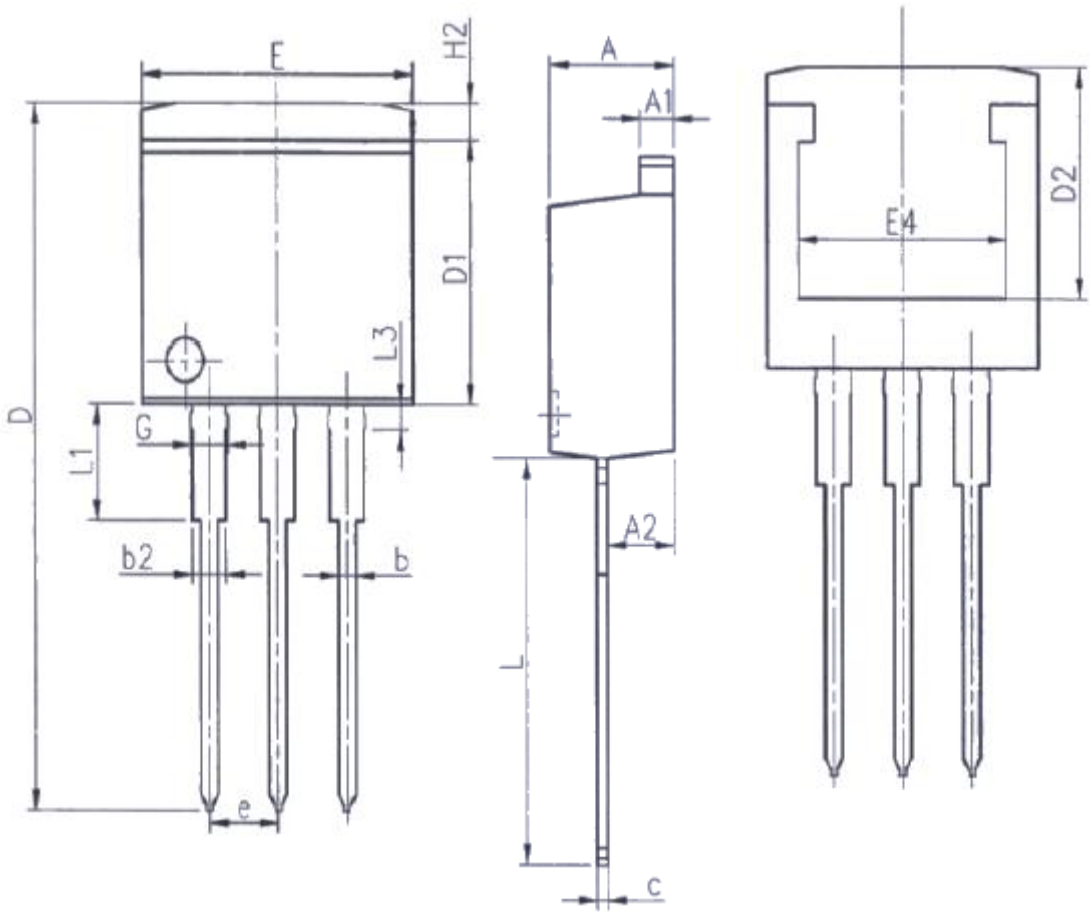
TO-263



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.22	1.42
A2	2.49	2.89
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.50	8.90
D4	6.60	-

Unit: mm		
Symbol	Min.	Max.
E	9.86	10.36
E5	7.06	-
e	2.54BSC	
H	14.70	15.50
H2	1.07	1.47
L	2.00	2.60
L1	1.40	1.70
L4	0.25BSC	
θ	0°	9°

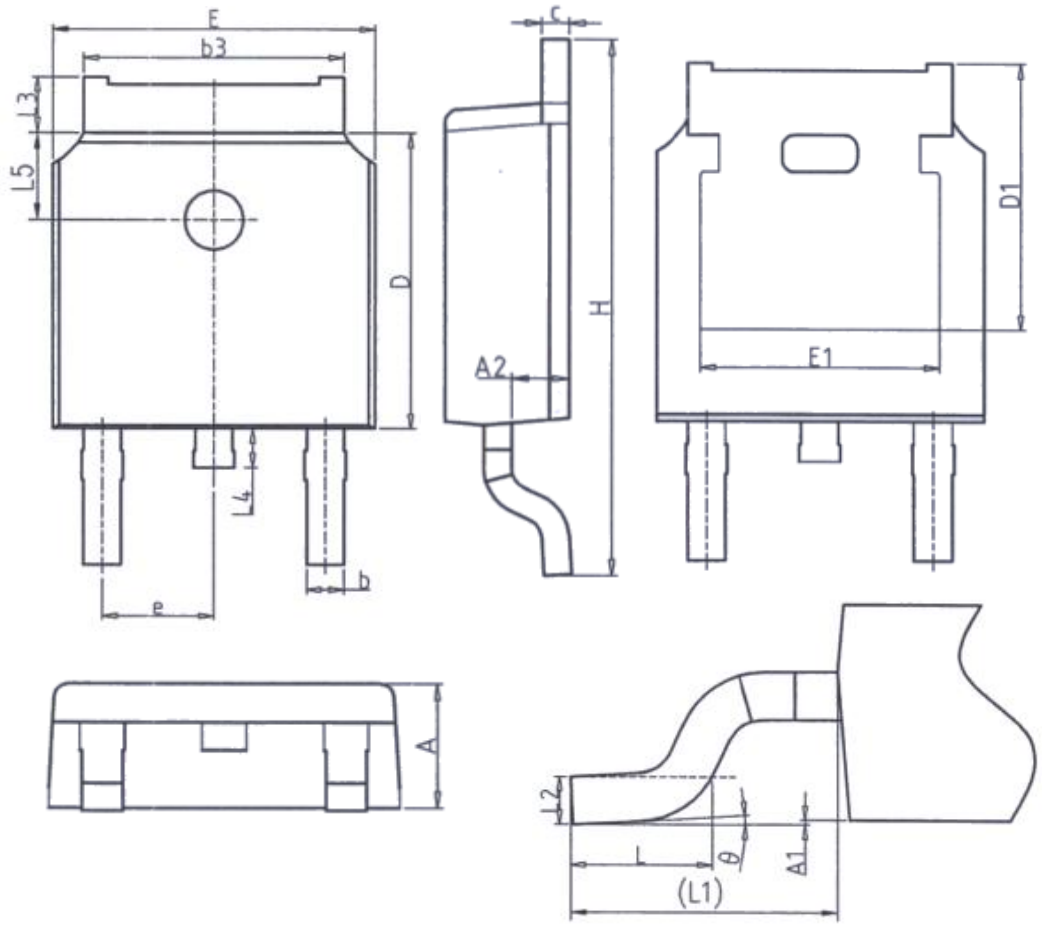
TO-262



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.22	1.42
A2	2.47	2.87
b	0.70	0.97
b2	1.17	1.42
c	0.28	0.53
D	23.20	24.02
D1	8.38	8.90
D2	6.00	-

Unit: mm		
Symbol	Min.	Max.
E	9.90	10.39
E4	7.30	-
e	2.54BSC	
G	1.25	1.50
H2	-	1.31
L	13.34	14.10
L1	3.30	4.06
L3	0.95	1.15

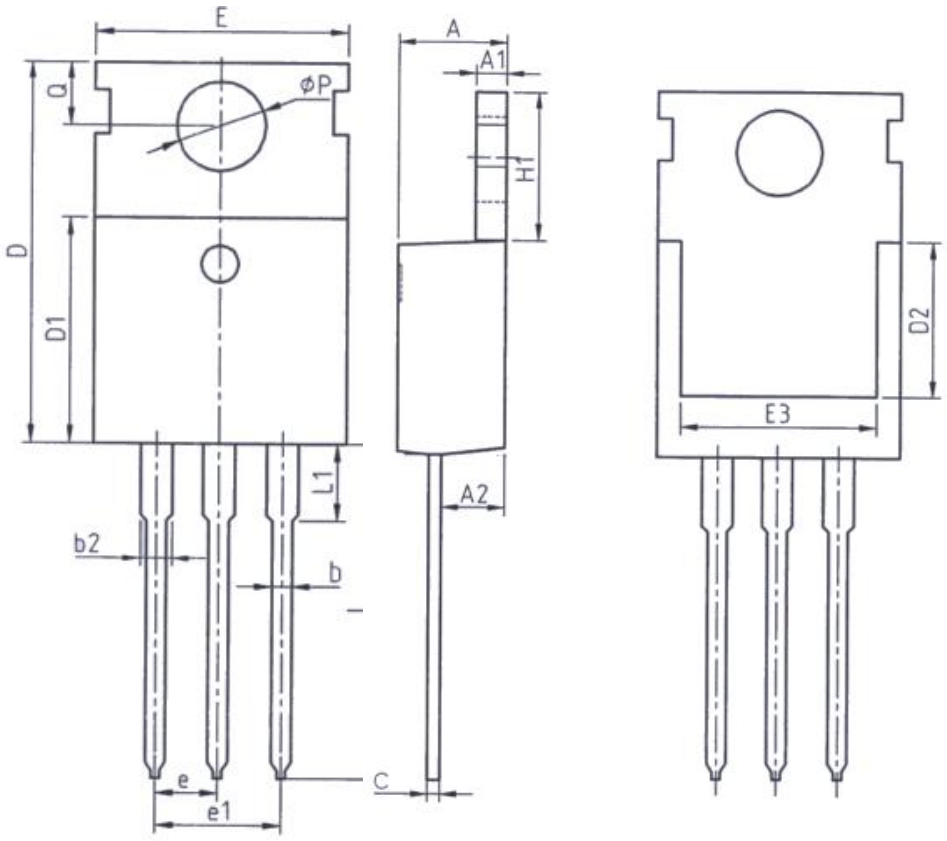
TO-252



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	–

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	–	1.00
L5	1.65	1.95
θ	0°	8°

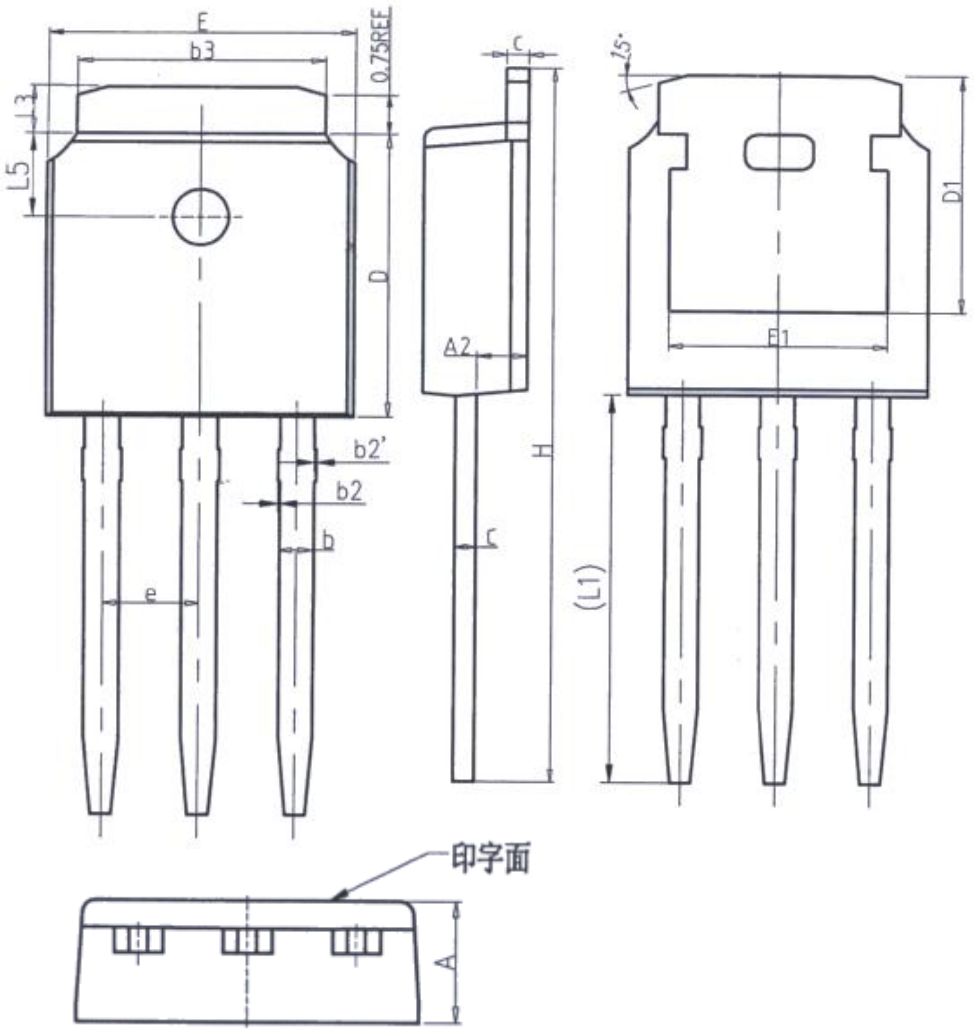
TO-220



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	–

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	–
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	–	3.40
P	3.40	3.80
Q	2.60	3.00

TO-251



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2′	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95

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